

Features

- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.26pF typical
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: ±20kV
Contact discharge: ±15kV
 - IEC61000-4-4 (EFT) 40A (5/50ns)
 - IEC61000-4-5 (Lightning) 4A (8/20µs)
- RoHS Compliant

Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

Part Number Code

E	S	D	0	5	1	1	L	1
1	2	3	4	5	6	7	8	9

Product Type	
ESD	TSK Electrostatic suppressor ESD Type

Reverse Working Voltage (V)	
3V3	3.3V
05	5V
16	16V

Line	
1	1-Line
2	2-Line
3	3-Line

Capacitance Type	
L	Low
X	Normal

directional	
0	Bi
1	Uni

Size	
1	0201
2	0402
3	DFN0603
4	DFN1006

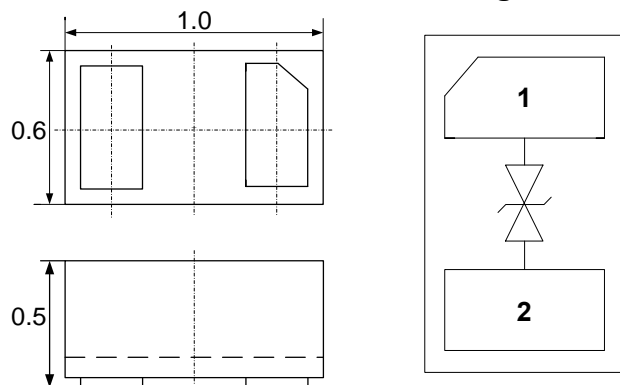
★ Code 4 to 9 is optional

Description

The ESD0510L4 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESD0510L4 has an ultra-low capacitance with a typical value at 0.26pF, and complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make ESD0510L4 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.



Dimensions and Pin Configuration



Package Dimensions

Circuit and Pin Schematic

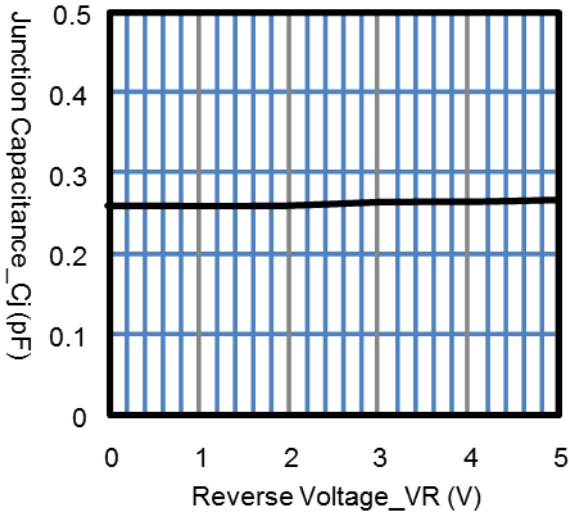
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	80	W
Peak Pulse Current (8/20 μs)	I _{PP}	4	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 20	kV
ESD per IEC 61000-4-2 (Contact)		± 15	
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

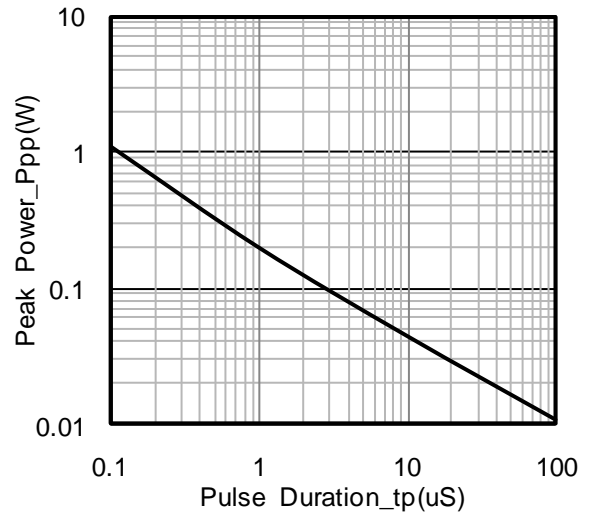
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	6	8	9	V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 5V
Clamping Voltage	V _C			12	V	I _{PP} = 1A (8 x 20 μs pulse)
Clamping Voltage	V _C			20	V	I _{PP} = 4A (8 x 20 μs pulse)
Junction Capacitance	C _J		0.26	0.35	pF	V _R = 0V, f = 1MHz

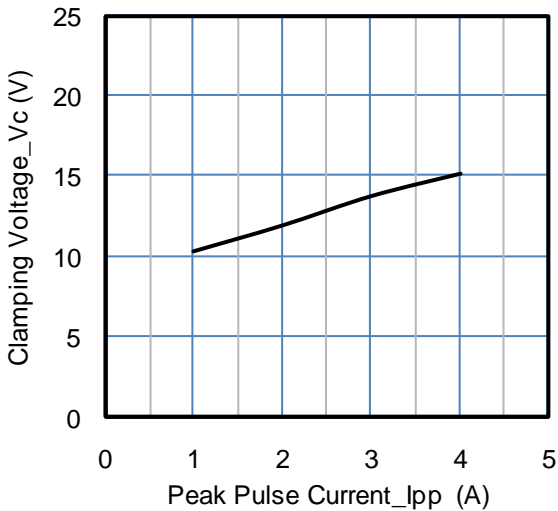
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



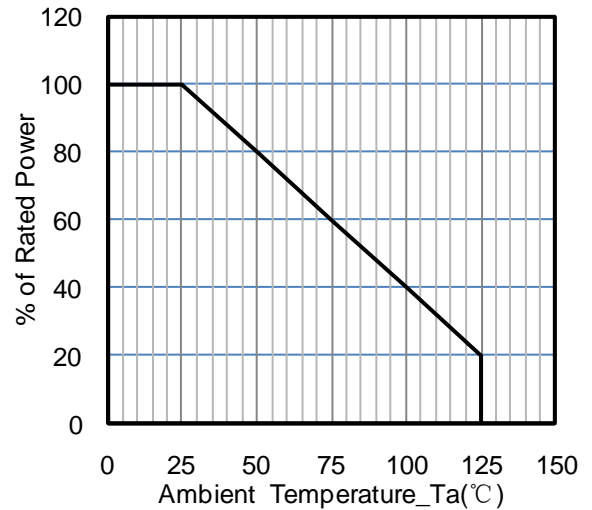
Junction Capacitance vs. Reverse Voltage



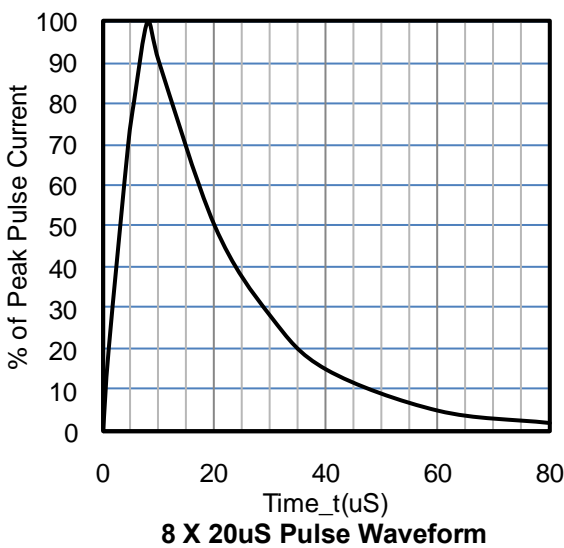
Peak Pulse Power vs. Pulse Time



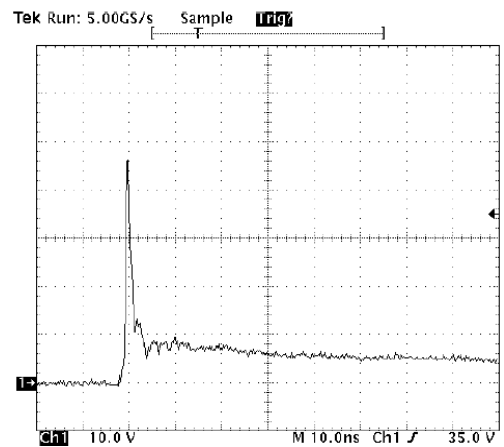
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



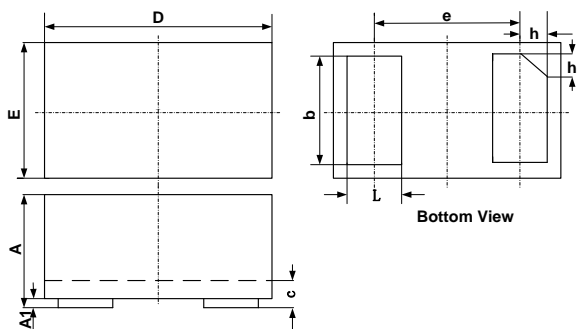
8 X 20uS Pulse Waveform



ESD Clamping Voltage

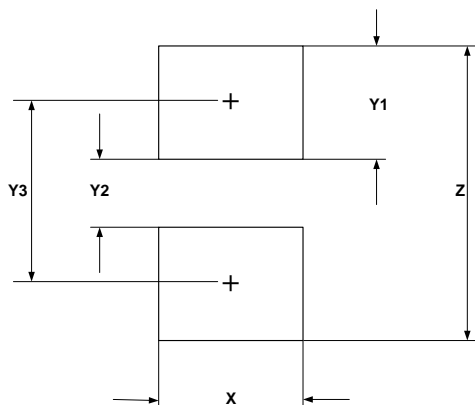
8 kV Contact per IEC61000-4-2

DFN1006-2 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

Ordering Information

Part Number	Packaging	Reel Size
ESD0510L4	10000/Tape & Reel	7 inch